2N3634 thru 2N3637

JAN, JTX AVAILABLE
CASE 79, STYLE 1
TO-39 (TO-39-205AD)

HIGH VOLTAGE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3634 2N3635	2N3636 2N3637	Unit
Collector-Emitter Voltage	V_{CEO}	140	175	Vdc
Collector-Base Voltage	V_{CBO}	140	175	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	 140 175	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CBO}$	 140 175	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 0.1 mAdc, V_{CE} = 10 Vdc)	2N3634, 2N3636 2N3635, 2N3637	h_{FE}	 40 80	 — —	—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	2N3634, 2N3636 2N3635, 2N3637		 45 90	 — —	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	2N3634, 2N3636 2N3635, 2N3637		 50 100	 — —	
(I_C = 50 mAdc, V_{CE} = 10 Vdc)	2N3634, 2N3636 2N3635, 2N3637		 50 100	 150 300	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)	2N3634, 2N3636 2N3635, 2N3637		 25 50	 — —	
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	 — —	 0.3 0.5	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	 — 0.65	 0.8 0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (V_{CE} = 30 Vdc, I_C = 30 mAdc, f = 100 MHz)	2N3634, 2N3636 2N3635, 2N3637	f_T	 150 200	 — —	MHz

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	10	pF
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	75	pF
Input Impedance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3634, 2N3636 2N3635, 2N3637	h_{ie}	100 200	600 1200	ohms
Voltage Feedback Ratio (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	—	3.0	X 10^{-4}
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3634, 2N3636 2N3635, 2N3637	h_{fe}	40 80	160 320	—
Output Admittance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	—	200	μmhos
Noise Figure (I_C = 0.5 mAdc, V_{CE} = 10 Vdc, R_S = 1.0 k ohms, f = 1.0 kHz)		NF	—	3.0	dB

SWITCHING CHARACTERISTICS

Turn-On Time	(V_{CC} = 100 Vdc, V_{BE} = 4.0 Vdc,	t_{on}	—	400	ns
Turn-Off Time	I_C = 50 mAdc, I_{B1} = I_{B2} = 5.0 mAdc)	t_{off}	—	600	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — JUNCTION CAPACITANCE VARIATIONS

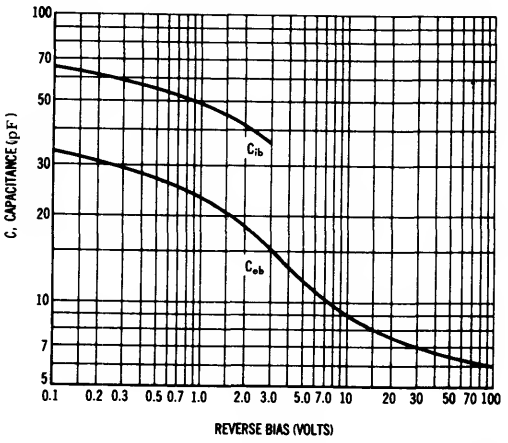


FIGURE 2 — GAIN-BANDWIDTH PRODUCT

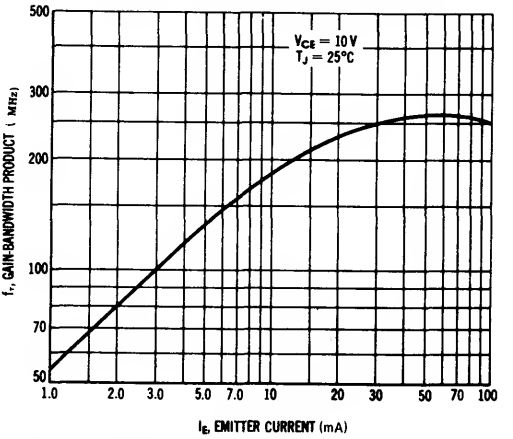
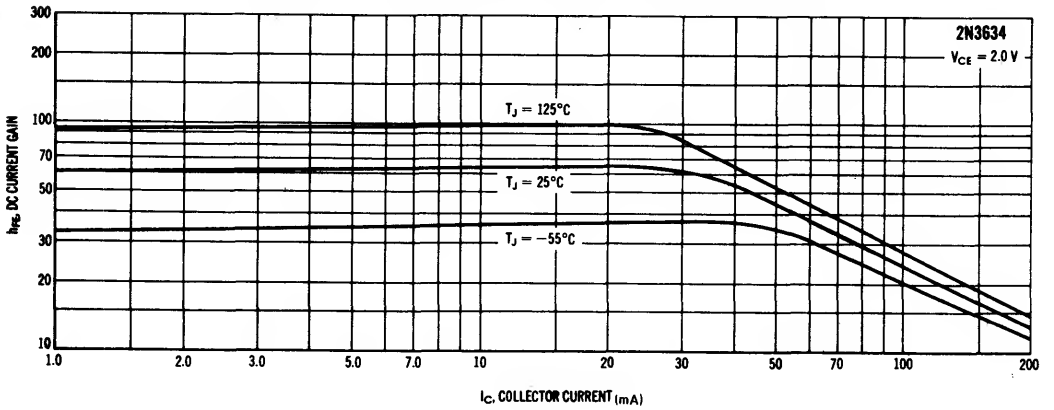


FIGURE 3 — CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE



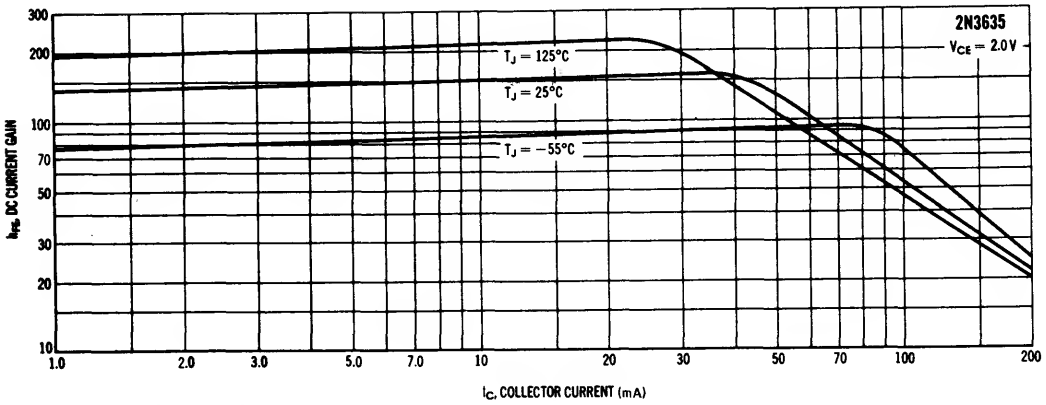


FIGURE 4 — CURRENT GAIN CHARACTERISTICS versus COLLECTOR EMITTER VOLTAGE

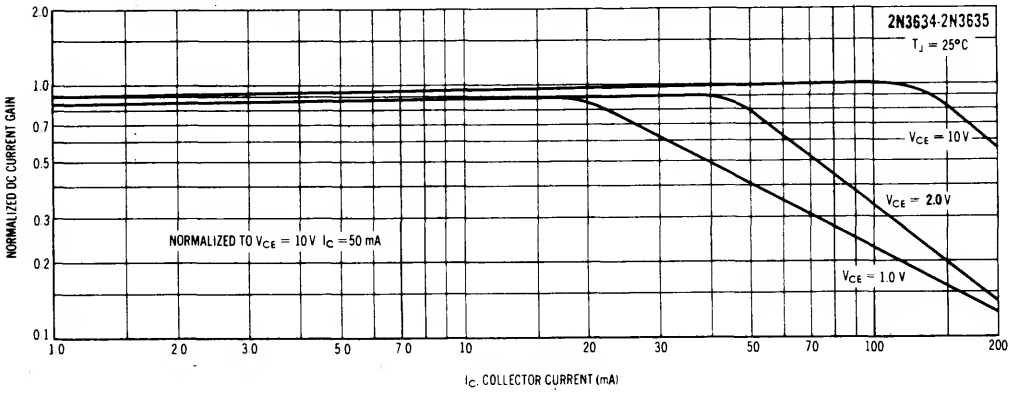
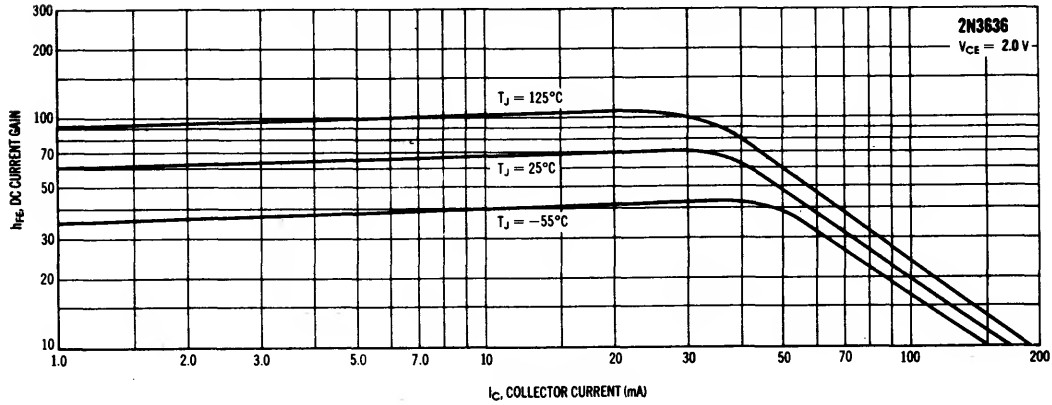


FIGURE 5 — CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE



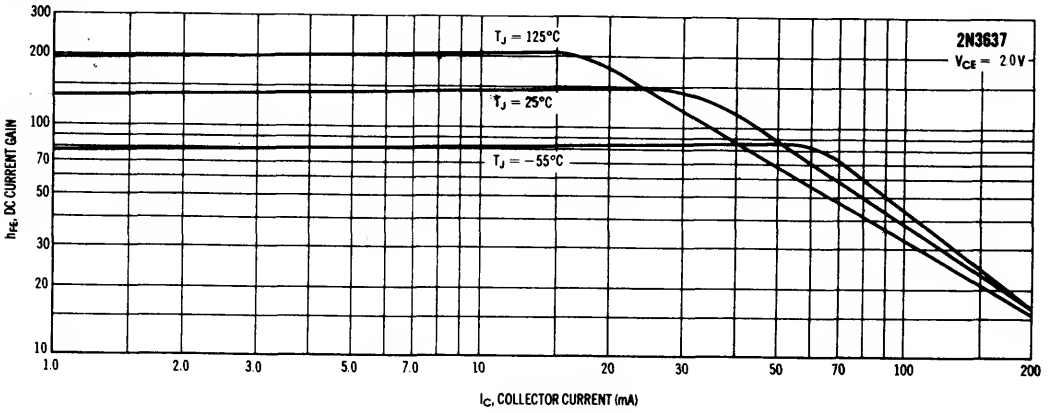


FIGURE 6 — CURRENT GAIN CHARACTERISTICS versus COLLECTOR EMITTER VOLTAGE

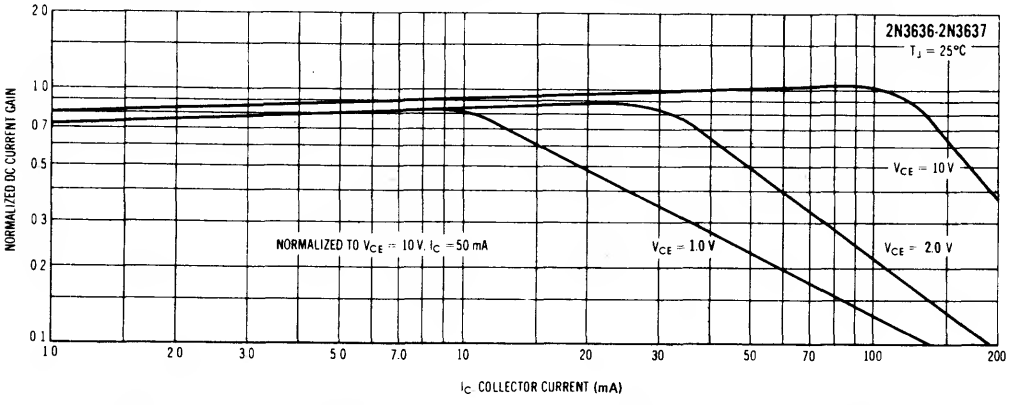


FIGURE 7 — INPUT IMPEDANCE

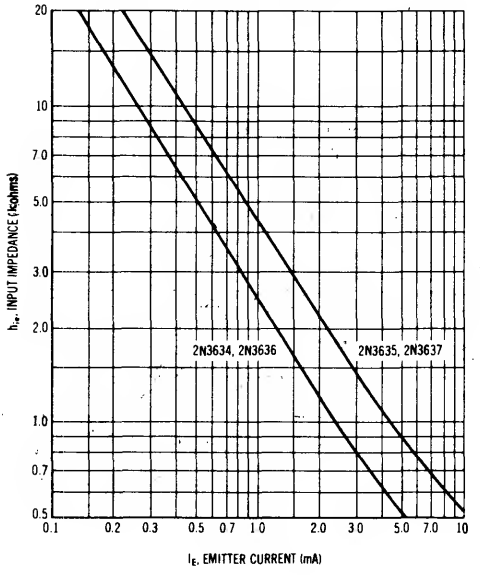


FIGURE 8 — OUTPUT IMPEDANCE

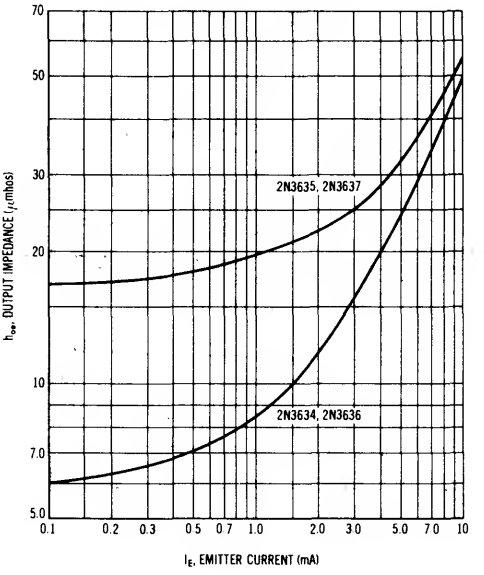


FIGURE 9 — CURRENT GAIN

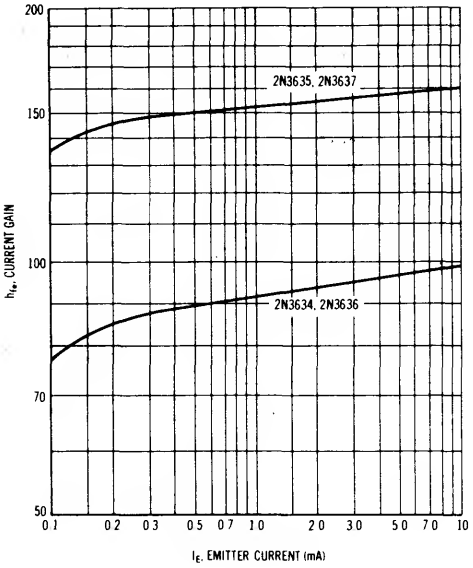


FIGURE 10 — VOLTAGE FEEDBACK RATIO

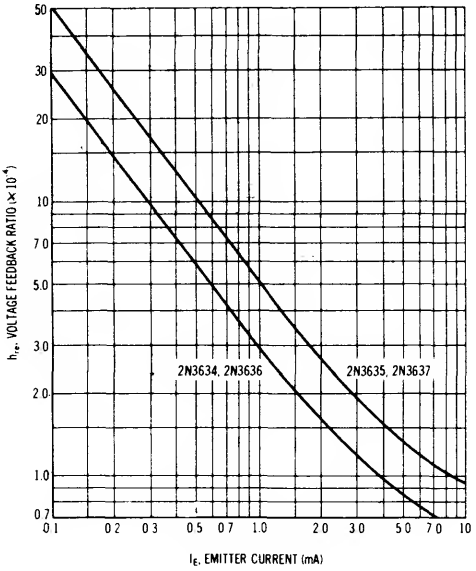


FIGURE 11 — SATURATION VOLTAGES

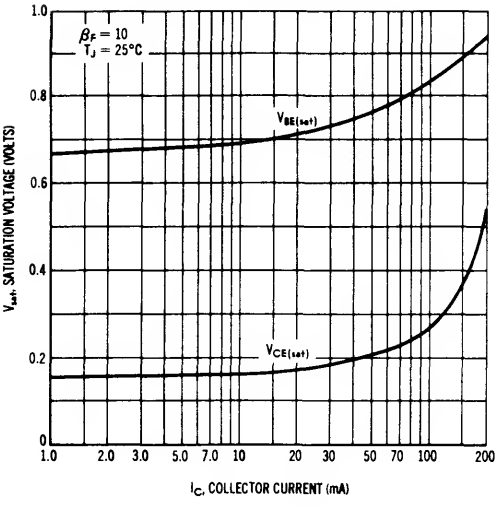


FIGURE 12 — TEMPERATURE COEFFICIENTS

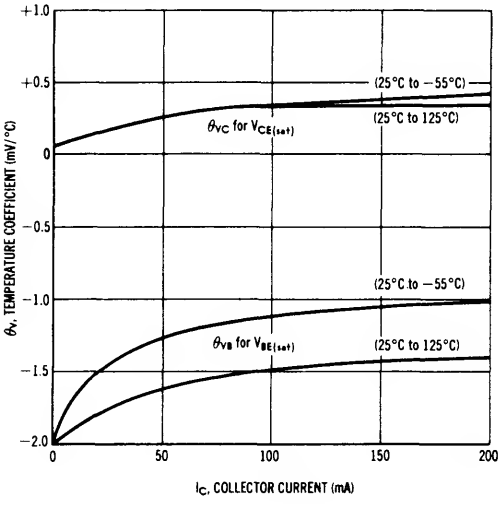
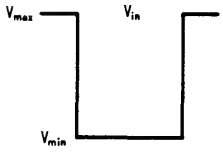


FIGURE 13 — SWITCHING TIME TEST CIRCUIT



P.W. ≅ 20 μs
DUTY CYCLE ≤ 2%
RISE TIME ≤ 20 ns

	V_{max}	V_{min}
TURN-ON	+4.0 V	−5.65 V
TURN-OFF	+4.1 V	−5.9 V

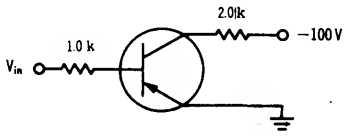


FIGURE 14 — TURN-ON TIME VARIATIONS WITH VOLTAGE

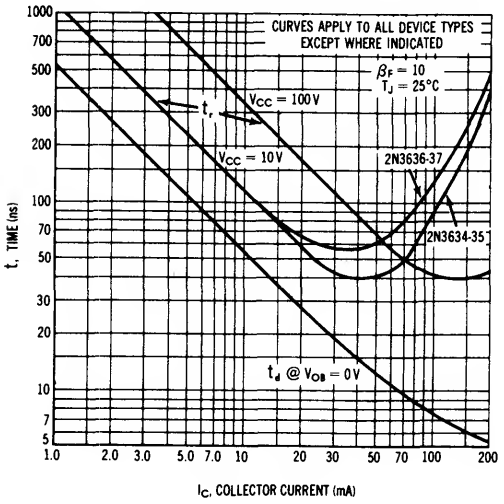
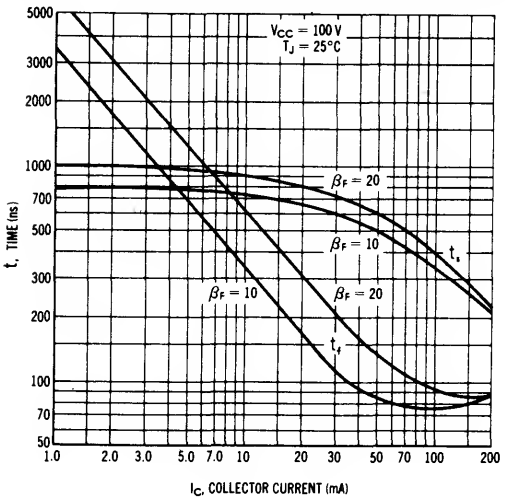


FIGURE 15 — TURN-OFF TIME VARIATIONS WITH CIRCUIT GAIN*



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2N3647, 2N3648 For Specifications, See 2N3510 Data.